

1SS82

Silicon Epitaxial Planar Diode for High Voltage Switching

HITACHI

ADE-208-149A (Z)

Rev. 1

Jul. 1995

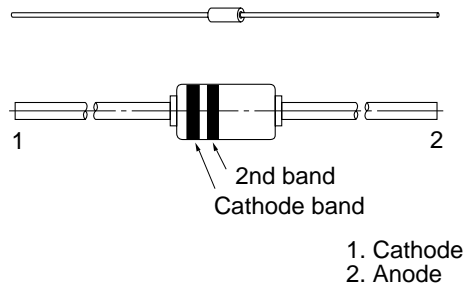
Features

- High reverse voltage. ($V_R = 200V$)
- High reliability with glass seal.

Ordering Information

Type No.	Cathode band	2nd band	Package Code
1SS82	Verdure	Light Blue	DO-35

Outline



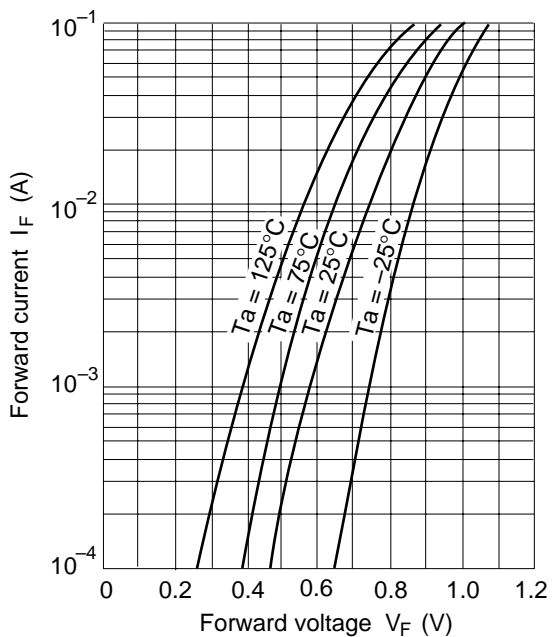
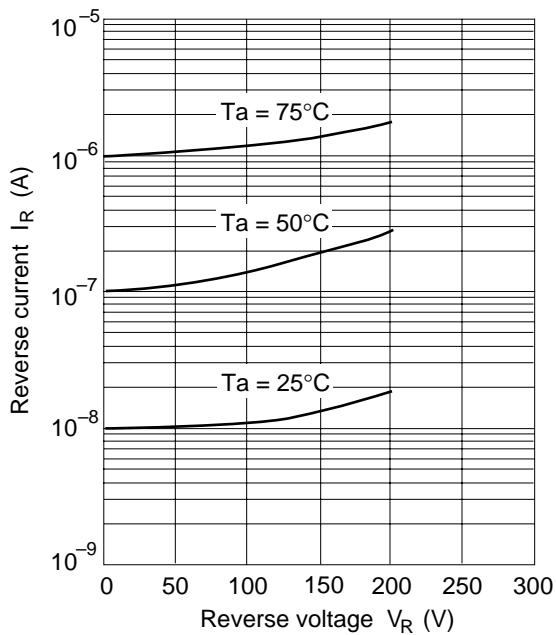
Absolute Maximum Ratings*2 (Ta = 25°C)

Item	Symbol	Value	Unit
Peak reverse voltage	V_{RM}^{*1}	250	V
Reverse voltage	V_R	200	V
Peak forward current	I_{FM}	625	mA
Non-Repetitive peak forward surge current	I_{FSM}^{*2}	1	A
Average forward current	I_O	200	mA
Power dissipation	Pd	400	mW
Junction temperature	Tj	175	°C
Storage temperature	Tstg	-65 to +175	°C

Notes: 1. Reverse voltage in excess of peak reverse voltage may deteriorate electrical characteristic.
 2. Within 1s forward surge current.

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	1.0	V	$I_F = 100\text{mA}$
Reverse current	I_{R1}	—	—	0.2	μA	$V_R = 200\text{V}$
	I_{R2}	—	—	100		$V_R = 250\text{V}$
Capacitance	C	—	1.5	—	pF	$V_R = 0\text{V}$, $f = 1\text{MHz}$
Reverse recovery time	t_{rr}	—	—	100	ns	$I_F = I_R = 30\text{mA}$, $I_{rr} = 3\text{mA}$, $R_L = 100\Omega$

**Fig.1 Forward current Vs. Forward voltage****Fig.2 Reverse current Vs. Reverse voltage**

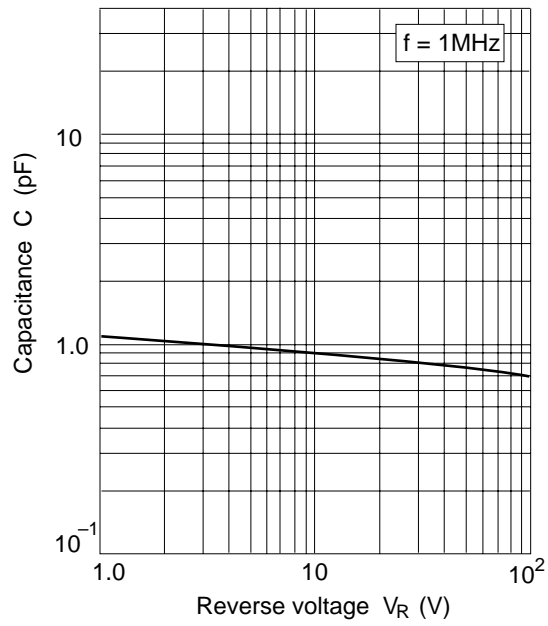
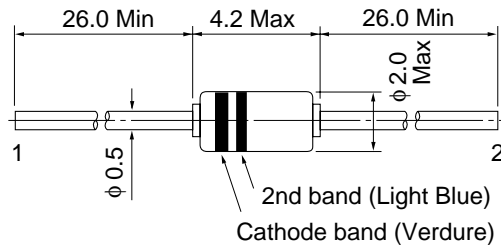


Fig.3 Capacitance Vs. Reverse voltage

Package Dimensions

Unit: mm



1 Cathode
2 Anode

HITACHI Code	DO-35
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JEDEC Code	DO-35
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EIAJ Code	SC-48
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Weight (g)	0.13
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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL North America : <http://semiconductor.hitachi.com/>
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building, No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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